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November 2013

FDB047N10

N-Channel PowerTrench[®] MOSFET 100 V, 164 A, 4.7 m Ω

Features

- $R_{DS(on)}$ = 3.9 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- · High Power and Current Handling Capability
- · RoHS Compliant

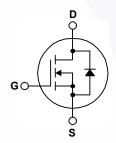
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- · Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Micro Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FDB047N10	Unit
V _{DSS}	Drain to Source Voltage		100	V
V_{GSS}	Gate to Source Voltage		±20	V
	Drain Current - Conti	nuous (T _C = 25°C, Silicon Limited)	164*	Α
I _D	- Cont	inuous (T _C = 100°C, Silicon Limited)	116*	Α
	- Cont	inuous (T _C = 25°C, Package Limited)	120	Α
I _{DM}	Drain Current - Pulsed (Note 1)		1) 656*	Α
E _{AS}	Single Pulsed Avalanche Energy	(Note	2) 1153	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note	3) 6.0	V/ns
D	Dower Dissipation	$(T_C = 25^{\circ}C)$	375	W
P_{D}	Power Dissipation	- Derate Above 25°C	2.5	W/°C
T _J , T _{STG}	Operating and Storage Temperate	Operating and Storage Temperature Range		
T_L	Maximum Lead Temperature for S	Soldering, 1/8" from Case for 5 Seconds	300	οС

^{*}Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

Thermal Characteristics

Symbol	Parameter	FDB047N10	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	
Б	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max. 62.5		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (1 in ² Pad of 2-oz Copper), Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDB047N10	FDB047N10	D ² -PAK	Tape and Reel	330 mm	24 mm	800 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	100	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.1	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	μА
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 150^{\circ}\text{C}$	-	-	500	μΑ
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(t}	h)	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.5	3.5	4.5	V
R _{DS(c}	on)	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 75 \text{ A}$	-	3.9	4.7	mΩ
g _{FS}		Forward Transconductance	$V_{DS} = 10 \text{ V}, I_{D} = 75 \text{ A}$	-	170	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V	-	11500	15265	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	-	1120	1500	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12	1	455	680	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time			-	174	358	ns
t _r	Turn-On Rise Time	$V_{DD} = 50 \text{ V}, I_{D} = 75 \text{ A},$		-	386	782	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{G} = 25 \Omega$		-	344	698	ns
t _f	Turn-Off Fall Time		(Note 4)	-	244	499	ns
Q _{g(tot)}	Total Gate Charge at 10V	V _{DO} = 80 V I _D = 75 A		-	160	210	nC
Q _{gs}	Gate to Source Gate Charge	V _{DS} = 80 V, I _D = 75 A, V _{GS} = 10 V		-	56	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	36	-	nC

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Dioc	Maximum Continuous Drain to Source Diode Forward Current		-	164*	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	656	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 75 A	-	-	1.25	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 75 A,	-	88	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	245	_	nC

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 0.41 mH, I $_{AS}$ = 75 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- 3. $I_{SD} \le 75$ A, di/dt ≤ 200 A/ μs , $V_{DD} \le BV_{DSS}$, starting $T_J = 25^{\circ}C$.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

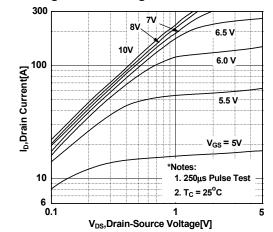


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

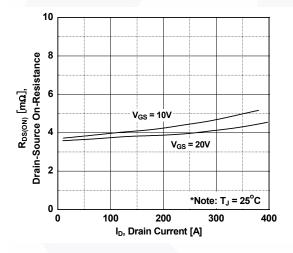


Figure 5. Capacitance Characteristics

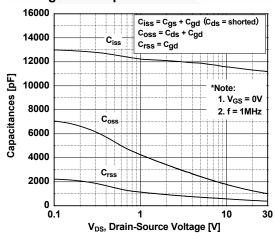


Figure 2. Transfer Characteristics

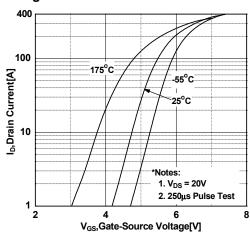


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

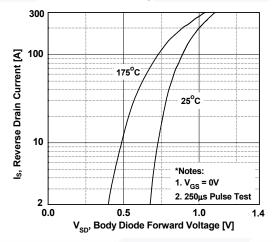
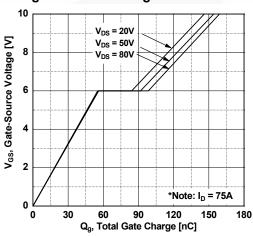


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

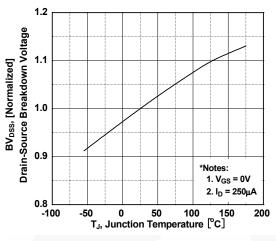


Figure 9. Maximum Safe Operating Area

Figure 8. On-Resistance Variation vs. Temperature

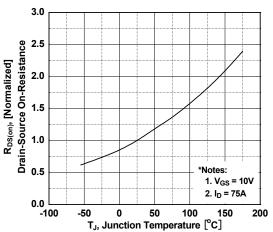
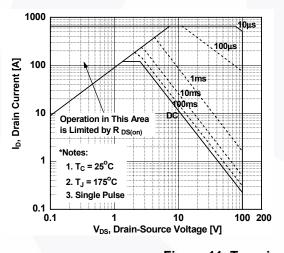


Figure 10. Maximum Drain Current vs. Case Temperature



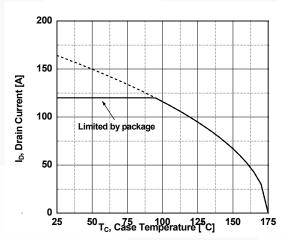
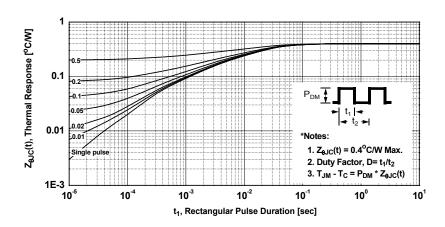


Figure 11. Transient Thermal Response Curve



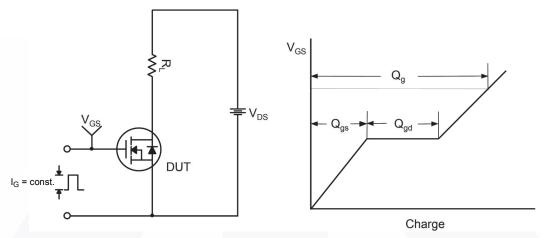


Figure 12. Gate Charge Test Circuit & Waveform

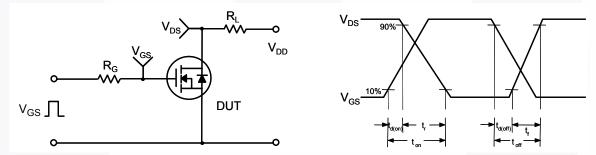


Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

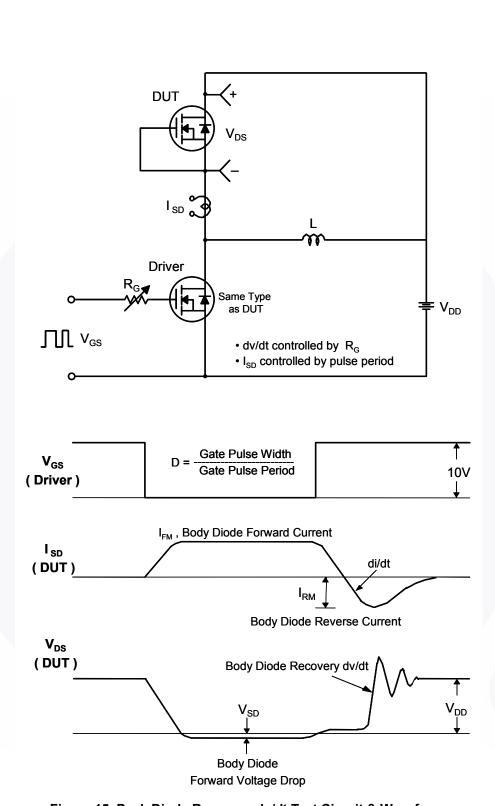


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

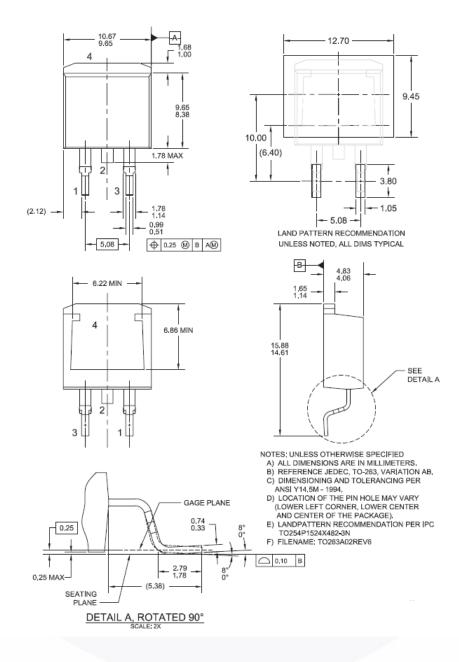


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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